

1. Scope :

This specification applies to silicon zener double diodes chips,
Device NO. SD-511A6G

2. Application :

The thermal path shall be electrically neutral within the package, Zener diode chip must be mounted on the thermal path and isolated the metal electrodes electrically.

3. Structure :

- 2-1. Planar type : P/N/P, Zener Double Diodes.
- 2-2. Electrodes :
Top side : Gold pad .
Back side : Isolation layer.

4. Size :

- 3-1. *Chip size : 11.0 mils x 11.0 mils (0.280 mm x 0.280 mm).
- 3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.025 mm).
- 3-3. Active area : 7.3 mils x 7.3 mils x 1/2 x 2 (0.186 mm x 0.186 mm x 1/2 x 2).
- 3-4. Dual Bonding pad : 6.8 mils x 6.8 mils x 1/2 x 2 (0.173 mm x 0.173 mm x 1/2 x 2) .
Height of hypotenuse : 5.23 mils (0.133 mm)
- 3-5. Pattern drawing : Refer to the attached drawing.

*Including scribing line. The chip size is about $(0.250 \pm 0.015)^2 \text{mm}^2$ after dicing.

5. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	$V_R=20V$ $E_e=0\text{mW/cm}^2$			0.5	μA
Zener Voltage	V_Z	$I_Z=5\text{mA}$ $E_e=0\text{mW/cm}^2$	23		29	V

